

ABSTRACT OF THE DISCLOSURE

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The present invention provides a nonvolatile memory that can be integrally formed with other semiconductor devices and can be reduced in size. A memory TFT, a switching TFT and other peripheral circuits constituting a nonvolatile memory are  
5 integrally formed on a substrate by TFTs. The memory TFT and the switching TFT are formed on the same semiconductor active layer, and a semiconductor active layer of the memory TFT is formed thinner than semiconductor active layers of the other TFTs. As a result, a nonvolatile memory that is hardly deteriorated and that can be reduced in size is provided, in which writing/erasing for the memory TFT can be realized at a low voltage.